## **Supplementary Information**

## Spontaneous interface engineering for dopant-free poly (3hexylthiophene) perovskite solar cells with efficiency over 24 %

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**Supplementary Figure 1.** TR-PL fitting data excluded initial time decay of (a) PRV/PS and (b) PRV/GA-PS.

The time-dependent charge carrier kinetics can be described by following equation<sup>1</sup>

$$\frac{dn}{dt} = -k_1 n - k_2 n^2 - k_3 n^3 \tag{1}$$

where *n* is the charge carrier density, and  $k_1$ ,  $k_2$ ,  $k_3$  are the rate constants for first-order (monomolecular), second-order (bimolecular), and third-order (auger) recombination constant, respectively. A single-mode pulsed diode laser (470 nm with a pulse width of ~30 ps, repetition rate of 500 kHz, and an average power of ~50 nW) was used as an excitation source. According to the conditions mentioned above, the TR-PL measurement was conducted at a fluence of 16.4  $\mu$ J/cm<sup>2</sup> with 470 nm wavelength (photon fluence: 2.8 x 10<sup>13</sup> photon/cm<sup>2</sup>). The calculated photoexcited carrier density (n<sub>0</sub>) by the laser pulse was 6.4 x 10<sup>17</sup> photon/cm<sup>3</sup>, while under the condition auger recombination is negligible. Thus, the first-order and the second-order recombination constants were shown in Supplementary Table 1.

$$n(t) = \frac{k_1 n_0 e^{-k_1 t}}{k_1 + k_2 n_0 \left(1 - e^{-k_1 t}\right)}$$
(2)

where n(t) is time dependent photoexcited charge carrier density, which is proportional the PL decay (PL(t)  $\propto$  n(t)). The initial time decay related to the third-order recombination was excluded and the validation of the TR-PL fitting was confirmed via the reduced - Chi square.

**Supplementary Table 1.** Calculated lifetime and recombination constants fitted from the PL decay of PRV/PS and PRV/GA-PS.

condition	Lifetime (ns)	<i>k</i> 1	$k_2$	reduced Chi-square
PRV/PS	108.3	9.23 x 10 <sup>6</sup>	1.24 x 10 <sup>-10</sup>	1.16
PRV/GA-PS	298.6	3.35 x 10 <sup>6</sup>	6.22 x 10 <sup>-11</sup>	1.10



**Supplementary Figure 2**. The cross-sectional SEM image of the device with FTO/SnO<sub>2</sub>/PRV/GA-P3HT structure.



**Supplementary Figure 3.** Statistics of photovoltaic parameters for 20 PSCs measured along reverse and forward bias scanning direction; (a) Short-circuit current density, (b) open-circuit voltage, (c) fill factor and (d) power conversion efficiency.



**Supplementary Figure 4.** (a) J-V curves and (b) EQE spectra of perovskite solar cells with pristine P3HT (control), 1, 3, and 6 mg of Ga(acac)<sub>3</sub> incorporated P3HT as a hole transport layer, respectively.

Supplementary	Table	2.	Photovoltaic	parameters	of	perovskite	solar	cells	corresponding	with
Supplementary F	igure 4.									

Scan direction	J <sub>SC</sub> (mA/cm <sup>2</sup> )	<i>V</i> <sub>OC</sub> (V)	FF (%)	PCE (%)	PCE <sub>avg</sub> *(%)
rev.	24.6	1.00	57.2	14.1	15.6
fwd.	24.8	1.00	69.1	17.1	15.0
rev.	25.2	1.09	75.8	20.8	21.2
fwd.	25.2	1.10	78.6	21.8	21.5
rev.	24.5	1.06	63.4	16.5	17.6
fwd.	24.8	1.07	70.6	18.7	17.0
rev.	24.4	1.06	60.4	15.6	16.0
fwd.	24.6	1.06	69.0	18.0	10.8
	Scan direction rev. fwd. rev. fwd. rev. fwd. rev. fwd. rev. fwd.	Scan direction         J <sub>SC</sub> (mA/cm <sup>2</sup> )           rev.         24.6           fwd.         24.8           rev.         25.2           fwd.         25.2           fwd.         25.2           fwd.         24.5           fwd.         24.8           rev.         24.5           fwd.         24.8           fwd.         24.8           fwd.         24.8           fwd.         24.4           fwd.         24.6	Scan directionJSC (mA/cm²)WOC (V)rev.24.61.00fwd.24.81.00rev.25.21.09fwd.25.21.10rev.24.51.06fwd.24.81.07rev.24.41.06fwd.24.61.06	Scan direction $J_{SC}$ (mA/cm²) $V_{OC}$ (V)FF (%)rev.24.61.0057.2fwd.24.81.0069.1rev.25.21.0975.8fwd.25.21.1078.6rev.24.51.0663.4fwd.24.81.0770.6rev.24.41.0660.4fwd.24.61.0669.0	Scan directionJsc (mA/cm²) $V_{OC}(V)$ FF (%)PCE (%)rev.24.61.0057.214.1fwd.24.81.0069.117.1rev.25.21.0975.820.8fwd.25.21.1078.621.8rev.24.51.0663.416.5fwd.24.81.0770.618.7rev.24.41.0660.415.6fwd.24.61.0669.018.0

† In 1 ml of P3HT solution; \* These values were calculated by averaging PCEs obtained from reverse and forward bias scanning.



**Supplementary Figure 5.** The solubility test of monovalent, divalent, and trivalent acetylacetonate in chlorobenzene. All chemicals were mixed with identical molar concentration.



**Supplementary Figure 6**. X-ray photoelectron spectra of the pristine perovskite and the perovskite films treated by the acetylacetonate (Acac), Al(acac)<sub>3</sub>, and Ga(acac)<sub>3</sub> for (a) Pb 4f, and (b) I 3d signals. (c) J-V curves of perovskite solar cells using P3HT incorporated with different metal acetylacetonates (control: pristine P3HT; A-P3HT: P3HT with Acac; AA-P3HT: P3HT with Al(acac)<sub>3</sub>; GA-P3HT: P3HT with Ga(acac)<sub>3</sub>).

Device	Scan direction	$J_{\rm SC}({ m mA/cm^2})$	$V_{\rm OC}({ m V})$	FF (%)	PCE (%)	PCE <sub>avg</sub> *(%)
aantral	rev.	24.6	1.00	57.2	14.1	15.6
control	fwd.	24.8	1.00	69.1	17.1	13.0
A-P3HT	rev.	24.6	0.99	63.4	15.4	16.2
	fwd.	24.7	1.00	68.3	16.9	16.2
	rev.	25.0	1.03	75.0	19.3	20.2
AA-P3H1	fwd.	25.1	1.04	81.0	21.1	20.2
GA-P3HT	rev.	25.2	1.09	75.8	20.8	21.2
	fwd.	25.2	1.10	78.6	21.8	21.3

**Supplementary Table 3**. Photovoltaic parameters of perovskite solar cells corresponding with Supplementary Figure 6c.

\* These values were calculated by averaging PCEs obtained from reverse and forward bias scanning.



**Supplementary Figure 7.** Current density-voltage (J-V) curves of perovskite solar cells with dopant free (a) spiro-OMeTAD, (b) PTAA and (c) PTB7\* hole transport layer.

\*PTB7: Poly [[4,8-bis[(2-ethylhexyl)oxy]benzo[1,2-b:4,5-b']dithiophene-2,6-diyl][3-fluoro-2-[(2-ethylhexyl)carbonyl]thieno[3,4-b]thiophenediyl ]]

НТМ	Ga(acac) <sub>3</sub> addition	Scan direction	$J_{\rm SC}$ (mA/cm <sup>2</sup> )	$V_{\rm OC}({ m V})$	FF (%)	PCE (%)
		rev.	24.0	1.00	36.6	8.8
spiro-	Х	fwd.	24.2	1.01	38.1	9.3
OMeTAD	0	rev.	24.5	1.03	65.9	16.6
	0	fwd.	24.7	1.05	68.9	17.9
	Х	rev.	23.4	0.97	48.7	11.1
PTAA		fwd.	23.1	1.01	61.2	14.3
	0	rev.	24.5	1.07	58.4	15.3
	0	fwd.	24.2	1.07	62.6	16.2
	PTB7 X	rev.	24.6	0.99	67.5	16.4
PTB7		fwd.	24.4	0.99	69.4	16.8
	0	rev.	25.1	1.01	77.0	19.5
	0	fwd.	25.0	1.00	78.0	19.5

Supplementary Table 4. Photovoltaic characteristics of PSCs with different HTMs.

**Supplementary Table 5**. TR-PL exponential fit parameter of P3HT and GA-P3HT films on the perovskite film.

condition	A <sub>1</sub>	<b>t</b> <sub>1</sub> ( <b>ns</b> )	A <sub>2</sub>	t <sub>2</sub> (ns)	$A_3$	t <sub>3</sub> (ns)	t <sub>avg</sub> (ns)
РЗНТ	8.4	0.418	0.27	9.6	0.06	53	20
GA-P3HT	54.7	0.352	-	-	-	-	0.352



**Supplementary Figure 8.** 2D carrier lifetime mapping images of (a) perovskite (PRV), (b) perovskite coated with P3HT (PRV/P3HT) and (c) perovskite coated with Ga(acac)<sub>3</sub>-mixed P3HT (PRV/GA-P3HT).

Supplementary Table 6. Calculated  $R_{sh}$ ,  $J_r$ , and  $J_d$  values of control and GA-P3HT devices.

condition	$\frac{R_{sh}}{(k\Omega \ cm^2)}$	$\frac{J_r}{(10^{-7} \mathrm{mA/cm^2})}$	$[10^{-9} \text{ mA/cm}^2)$
control	370	4.13	2.05
GA-P3HT	880	3.29	6.87



Supplementary Figure 9. Schematic model experimental procedure.



**Supplementary Figure 10.** AFM images of (a) P3HT (rms: 23.96 nm) and (b) GA-P3HT (rms: 21.68 nm) films on perovskite. The image dimension is  $5 \ \mu m \times 5 \ \mu m$ .



**Supplementary Figure 11.** (a) X-ray photoelectron spectra of the P3HT and  $Ga(acac)_3$ -mixed P3HT (GA-P3HT) samples for detecting S 2p signal. (b) UV-visible absorption spectra, (c) Raman spectra of the corresponding samples. (d) *J-V* curves of the hole-only devices with the configuration of ITO/PEDOT:PSS/polymer/MoO<sub>x</sub>/Ag. The measurements were performed under dark state.



**Supplementary Figure 12.** Water contact angle images on (a) pristine perovskite (PRV), (b) Ga(acac)<sub>3</sub>-treated perovskite, (c) pristine P3HT and (d) Ga(acac)<sub>3</sub>-mixed P3HT. All images were taken 1 second after loading the water droplets.



**Supplementary Figure 13.** PCE evolution of control and GA-P3HT devices under 10% relative humidity at 85°C. The devices were tested without encapsulation.



**Supplementary Figure 14.** TR-PL fitting data excluded initial time decay of (a) DHA/PS and (b) DHA/GA-PS.

**Supplementary Table 7.** Calculated lifetime and recombination constants fitted from the PL decay of DHA/PS and DHA/GA-PS.

condition	Lifetime (µs)	<i>k</i> 1	<b>k</b> <sub>2</sub>	reduced Chi-square
DHA/PS	1.86	5.36 x 10 <sup>5</sup>	5.32 x 10 <sup>-12</sup>	1.129
DHA/GA-PS	2.78	3.59 x 10 <sup>5</sup>	4.86 x 10 <sup>-12</sup>	1.041



**Supplementary Figure 15**. 2D carrier lifetime mapping images of (a) DHA/PS and (b) DHA/GA-PS films.



Supplementary Figure 16. Conductive AFM images of DHA and GA-treated DHA film. The image dimension is 5  $\mu$ m x 5  $\mu$ m.

## Reference

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